

General Description

These N-Channel enhancement mode power field effect transistors are produced using advanced technology. This latest technology has been especially designed to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power Supplier, active power factor correction based on Half-Bridge topology.

Features

- Originative New Design
- 100% avalanche tested
- Very Low Intrinsic Capacitances
- Fast switching
- Improved dv/dt capability
- 11A, 600V, $R_{DS(on)} = 0.75\Omega$ @ $V_{GS} = 10\text{ V}$

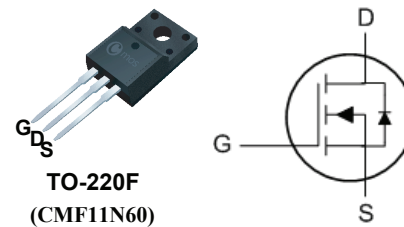
Product Summary

BVDSS	$R_{DS(on)}$	ID
600V	0.75Ω	11A

Applications

- Charger
- Adaptor
- Power Supply
- Electroless lamp

TO-220F Pin Configuration



Absolute Maximum Ratings

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	CMF11N60	Units
V_{DSS}	Drain-Source Voltage	600	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	11	A
		6.0	A
I_{DM}	Drain Current - Pulsed ¹	44	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy ²	709	mJ
E_{AR}	Repetitive Avalanche Energy ³	16.2	mJ
dv/dt	Peak Diode Recovery dv/dt	4.5	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	52	W
	- Derate above 25°C	0.40	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

¹ Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	CMF11N60	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case Max.	2.4	$^\circ\text{C/W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ.	---	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient Max.	62.5	$^\circ\text{C/W}$

Electrical Characteristic

 $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	600	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C	--	0.7	--	$V/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 480\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3.0	--	4.5	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 5.0\text{ A}$	--	0.62	0.75	Ω

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	1650	--	pF
C_{oss}	Output Capacitance		--	165	--	pF
C_{rss}	Reverse Transfer Capacitance		--	18	--	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 300\text{ V}, I_D = 11\text{ A}$ $R_G = 25\text{ }\Omega$ ^{4 5}	--	25	--	ns
t_r	Turn-On Rise Time		--	70	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	140	--	ns
t_f	Turn-Off Fall Time		--	80	--	ns
Q_g	Total Gate Charge	$V_{DS} = 480\text{ V}, I_D = 11\text{ A}$ $V_{GS} = 10\text{ V}$ ^{4 5}	--	48	--	nC
Q_{gs}	Gate-Source Charge		--	7.0	--	nC
Q_{gd}	Gate-Drain Charge		--	18	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	11	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	44	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 11A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 11A	--	430	--	ns
Q _{rr}	Reverse Recovery Charge	di _F / dt = 100 A/μs	--	4.3	--	μC

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L=13\text{ mH}$, $I_{AS}=10.0\text{ A}$, $V_{DD}=50\text{ V}$, $R_G=25\text{ }\Omega$, Starting $T_J=25^\circ\text{C}$
3. $I_{SD}\leq 10.0\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
5. Essentially Independent of Operating Temperature Typical Characteristics

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